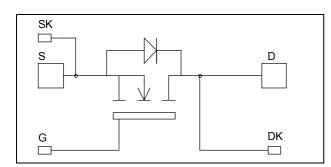


# Single Switch MOSFET Power Module

$$\begin{split} V_{DSS} &= 200V \\ R_{DSon} &= 3m\Omega \ typ \ @ \ Tj = 25^{\circ}C \\ I_D &= 580A \ @ \ Tc = 25^{\circ}C \end{split}$$



#### **Application**

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

#### **Features**

- Power MOS 7® FREDFETs
  - Low R<sub>DSon</sub>
  - Low input and Miller capacitance
  - Low gate charge
  - Fast intrinsic reverse diode
  - Avalanche energy rated
  - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
  - Symmetrical design
  - M5 power connectors
- High level of integration
- AlN substrate for improved thermal performance



- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Low profile
- RoHS Compliant

#### **Absolute maximum ratings**

Symbol	Parameter		Max ratings	Unit	
$V_{ m DSS}$	Drain - Source Breakdown Voltage		200	V	
т	Continuous Drain Current	$T_c = 25$ °C	580		
$I_D$	Continuous Drain Current	$T_c = 80$ °C	434	Α	
$I_{DM}$	Pulsed Drain current		2320		
$V_{GS}$	Gate - Source Voltage		±30	V	
$R_{DSon}$	Drain - Source ON Resistance		3.6	$m\Omega$	
$P_{D}$	Maximum Power Dissipation $T_c = 25^{\circ}C$		2270	W	
$I_{AR}$	Avalanche current (repetitive and non repetitive)		100	A	
E <sub>AR</sub>	Repetitive Avalanche Energy		50	m I	
$E_{AS}$	Single Pulse Avalanche Energy		3000	mJ	

These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



## All ratings @ $T_j = 25$ °C unless otherwise specified

## **Electrical Characteristics**

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 200V$ $T_j = 25^{\circ}C$			500	μА
		$V_{GS} = 0V, V_{DS} = 160V$ $T_j = 125^{\circ}C$			3000	
R <sub>DS(on)</sub>	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 290A$		3	3.6	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}$ , $I_D = 15$ mA	3		5	V
$I_{GSS}$	Gate – Source Leakage Current	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$			±400	nA

**Dynamic Characteristics** 

·	Characteristic	Test Conditions	Min	Тур	Max	Unit
$C_{iss}$	Input Capacitance	$V_{GS} = 0V$		43.3		
$C_{oss}$	Output Capacitance	$V_{DS} = 25V$		13.9		nF
$C_{rss}$	Reverse Transfer Capacitance	f = 1MHz		0.87		
$Q_{\mathrm{g}}$	Total gate Charge	$V_{GS} = 10V$		840		nC
$Q_{\mathrm{gs}}$	Gate – Source Charge	$V_{Bus} = 100V$		318		
$Q_{\mathrm{gd}}$	Gate – Drain Charge	$I_D = 580A$		402		
$T_{d(on)}$	Turn-on Delay Time	Inductive switching @ 125°C		32		
$T_{\rm r}$	Rise Time	$\begin{aligned} V_{GS} &= 15V \\ V_{Bus} &= 133V \\ I_D &= 580A \\ R_G &= 0.8\Omega \end{aligned}$		64		
$T_{d(off)}$	Turn-off Delay Time			88		ns
$T_{\mathrm{f}}$	Fall Time			116		
Eon	Turn-on Switching Energy	Inductive switching @ 25°C $V_{GS} = 15V$ , $V_{Bus} = 133V$ $I_D = 580A$ , $R_G = 0.8\Omega$		5		I
$\mathrm{E}_{\mathrm{off}}$	Turn-off Switching Energy			5.6		mJ
Eon	Turn-on Switching Energy	Inductive switching @ 125°C		5.6		
E <sub>off</sub>	Turn-off Switching Energy	$V_{GS} = 15V, V_{Bus} = 133V$ $I_D = 580A, R_G = 0.8\Omega$		5.9		mJ

### Source - Drain diode ratings and characteristics

Source - Drain Glode ratings and characteristics							
Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
$I_S$	Continuous Source current		$Tc = 25^{\circ}C$			580	A
	(Body diode)		$Tc = 80^{\circ}C$			434	A
$V_{\mathrm{SD}}$	Diode Forward Voltage	$V_{GS} = 0V, I_S = -580A$			1.3	V	
dv/dt	Peak Diode Recovery •					8	V/ns
t <sub>rr</sub>	Reverse Recovery Time	* 500 h	$T_j = 25^{\circ}C$			230	ns
	reverse receivery Time	$I_S = -580A$ $V_R = 500V$	$T_j = 125$ °C			450	115
Q <sub>rr</sub>	Reverse Recovery Charge	$di_{S}/dt = 600A/\mu s$	$T_j = 25^{\circ}C$		5.4		μС
	Reverse Recovery Charge		$T_j = 125$ °C		20.4		μΟ

• dv/dt numbers reflect the limitations of the circuit rather than the device itself.

 $I_S \leq \text{--} 580 A \qquad \text{di/dt} \leq 700 A/\mu s \qquad V_R \leq V_{DSS} \qquad T_j \leq 150 ^{\circ} C$ 

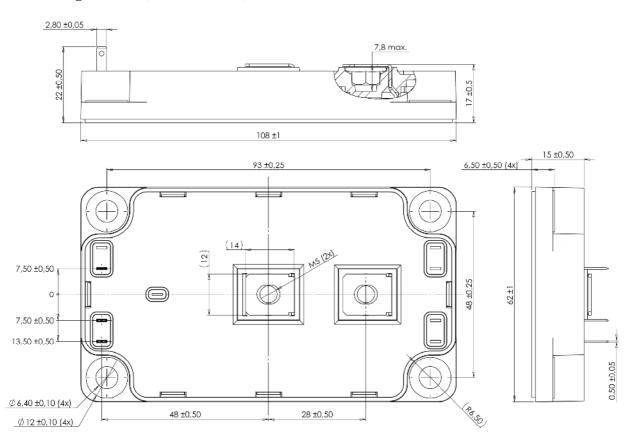
2 - 7



## Thermal and package characteristics

Symbol	Characteristic		Min	Тур	Max	Unit	
$R_{thJC}$	Junction to Case Thermal Resistance					0.055	°C/W
$V_{ISOL}$	RMS Isolation Voltage, any terminal to case t = 1 min, 50/60Hz			4000			V
$T_{J}$	Operating junction temperature range		-40		150		
T <sub>STG</sub>	Storage Temperature Range			-40		125	°C
$T_{\rm C}$	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M6	3		5	N.m
Torque		For terminals	M5	2		3.5	11.111
Wt	Package Weight					300	g

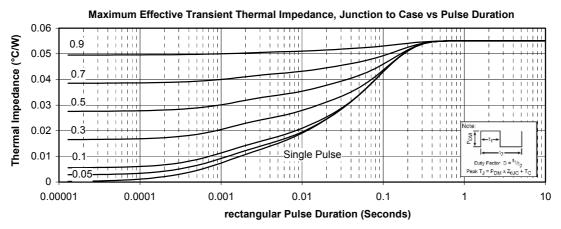
## SP6 Package outline (dimensions in mm)

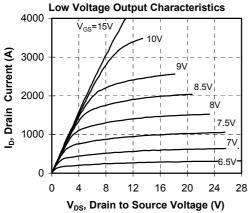


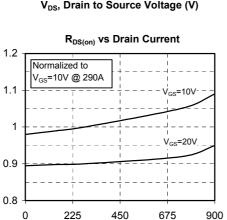
See application note APT0601 - Mounting Instructions for SP6 Power Modules on www.microsemi.com



## **Typical Performance Curve**

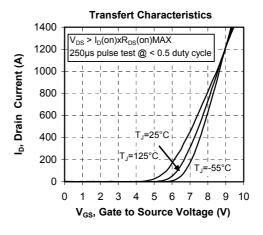


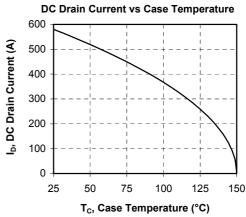




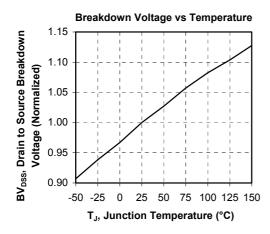
I<sub>D</sub>, Drain Current (A)

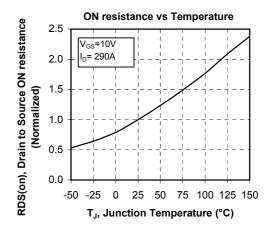
R<sub>DS(on)</sub> Drain to Source ON Resistance

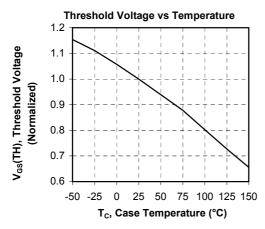


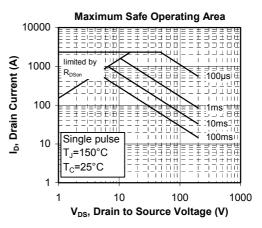


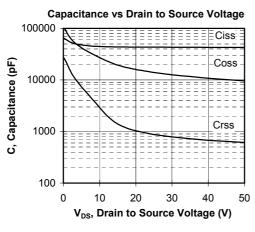


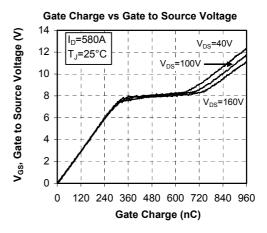






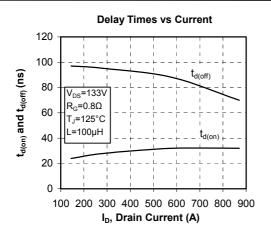


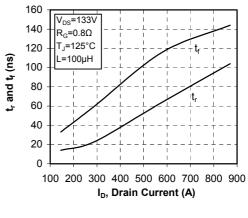


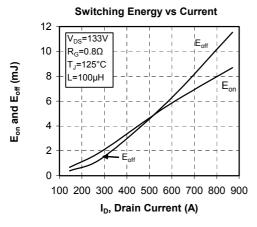


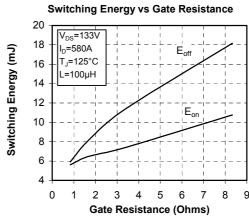


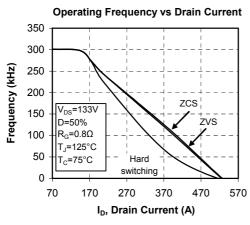
Rise and Fall times vs Current

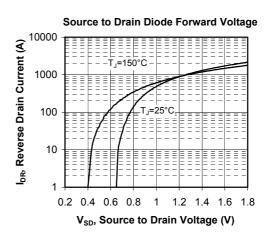












6 - 7

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